Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	12.5	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 45$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	0.2	-	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	0.2	-	5	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate		G sym051
3	T1	main terminal 1	3 2 1 TO-92 (SOT54)	, and the second

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
Z0103MA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 45$ °C; Fig. 1; Fig. 2; Fig. 3	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	13.8	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G+	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$ μ s; T2+ G-	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$ μ s; T2- G-	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$ μ s; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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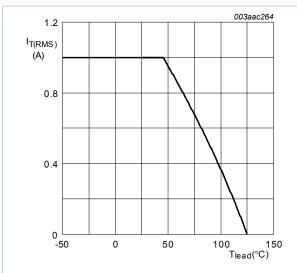
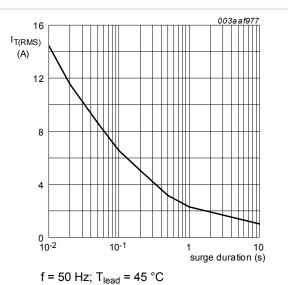


Fig. 1. RMS on-state current as a function of lead temperature; maximum values





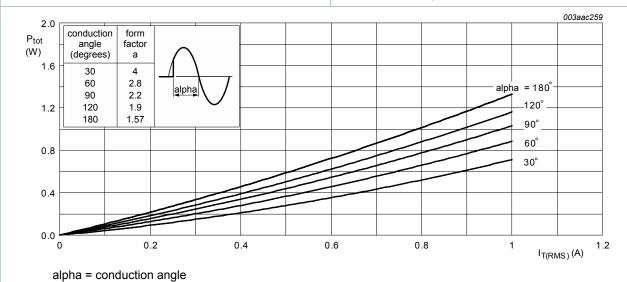


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

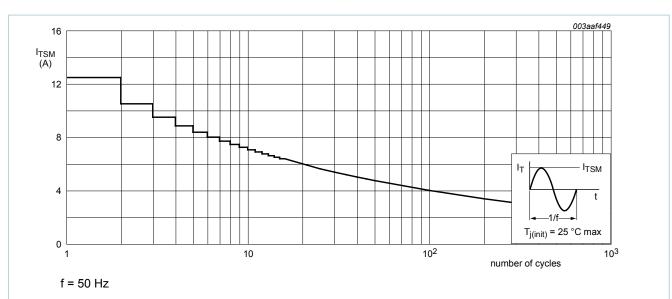


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

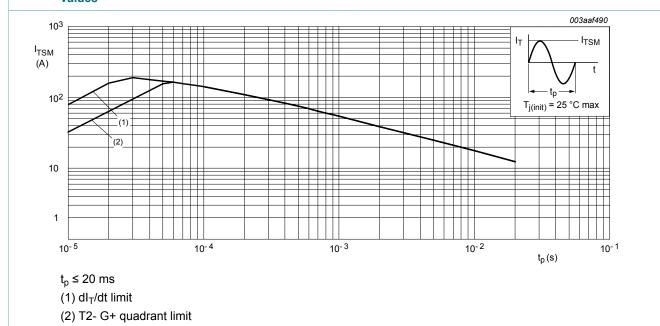


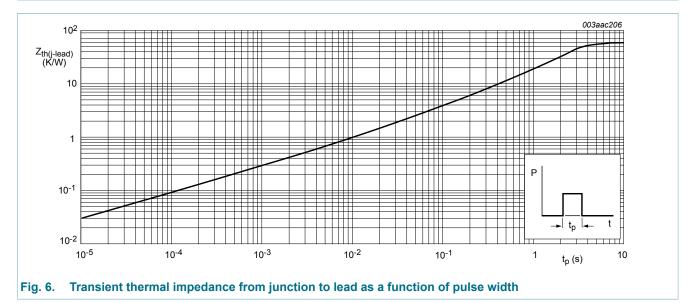
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; lead length 4 mm	-	150	-	K/W



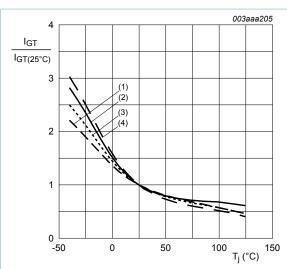
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	0.2	-	5	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	7	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	7	mA
Ін	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	7	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
$V_{ m GT}$	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	-	1	V
		V _D = 600 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	-	-	V
D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	80	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; $dI_{com}/$ dt = 0.44 A/ms; I_T = 1 A; gate open circuit	0.5	-	-	V/µs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

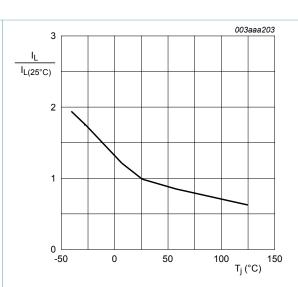


Fig. 8. Normalized latching current as a function of junction temperature

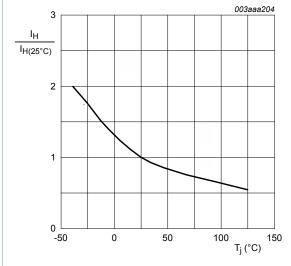
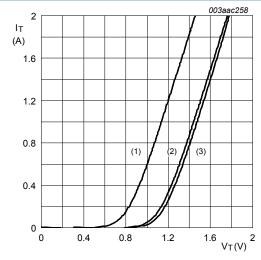
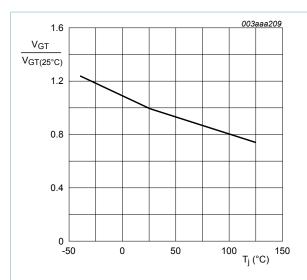


Fig. 9. Normalized holding current as a function of junction temperature



- $V_0 = 1.13 \text{ V}$
- $R_s = 0.31 \Omega$
- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



junction temperature

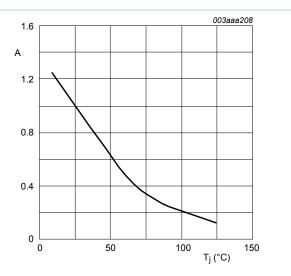


Fig. 11. Normalized gate trigger voltage as a function of Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{D(Tj\,^{\circ}\,C)}\,/\,\,dt}{d\mathrm{V}_{D(25\,^{\circ}\,C)}/\,\,dt}$$

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10. Package outline

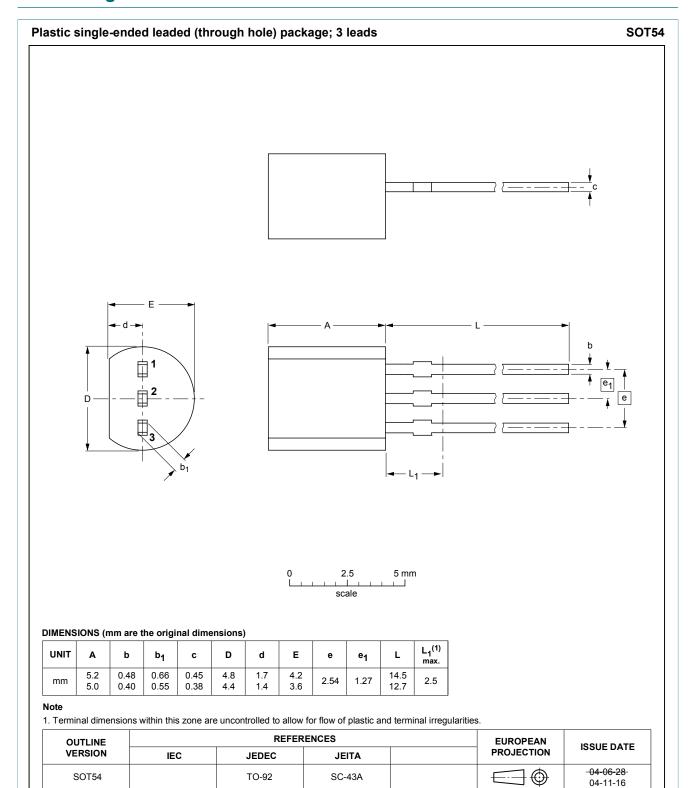


Fig. 13. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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